

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V_{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-40	-	-	V
Gate-body Leakage current	I_{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	V _{DS} = -40V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C		-	-	5	
Gate-Threshold Voltage	V_{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.6	-2.5	V
Drain-Source On-Resistance ⁴	R_{DS(on)}	V _{GS} = -10V, I _D = -16A	-	10	13	mΩ
		V _{GS} = -4.5V, I _D = -12A	-	14	20	
Forward Transconductance ⁴	g_{fs}	V _{DS} = -10V, I _D = -16A	-	44	-	S
Dynamic Characteristics⁵						
Input Capacitance	C_{iss}	V _{DS} = -20V, V _{GS} = 0V, f = 1MHz	-	3050	-	pF
Output Capacitance	C_{oss}		-	282	-	
Reverse Transfer Capacitance	C_{rss}		-	230	-	
Gate Resistance	R_g	f = 1MHz	-	9	-	Ω
Switching Characteristics⁵						
Total Gate Charge	Q_g	V _{GS} = -10V, V _{DS} = -20V, I _D = -16A	-	28	-	nC
Gate-Source Charge	Q_{gs}		-	8	-	
Gate-Drain Charge	Q_{gd}		-	8.5	-	
Turn-on Delay Time	t_{d(on)}	V _{GS} = -10V, V _{DD} = -15V, R _G = 3Ω, I _D = -16A	-	38	-	ns
Rise Time	t_r		-	31	-	
Turn-off Delay Time	t_{d(off)}		-	90	-	
Fall Time	t_f		-	9.2	-	
Drain-Source Body Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	I _S = -1A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	T _C =25°C	I_S	-	-	-30	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}= -25V, V_{GS}= -10V,L=0.1mH,I_{AS}= -40A.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test..

Typical Characteristics

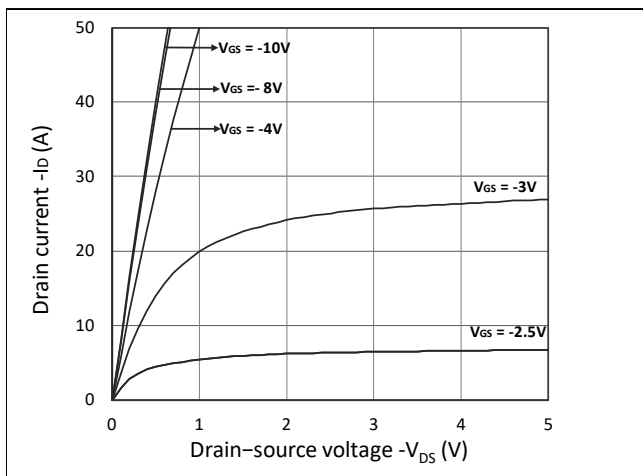


Figure 1. Output Characteristics

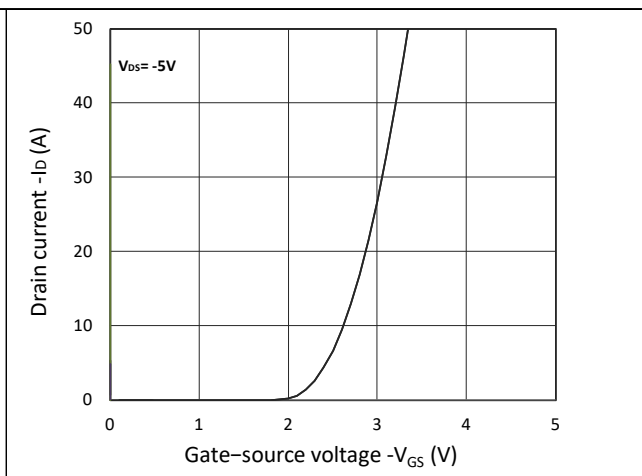


Figure 2. Transfer Characteristics

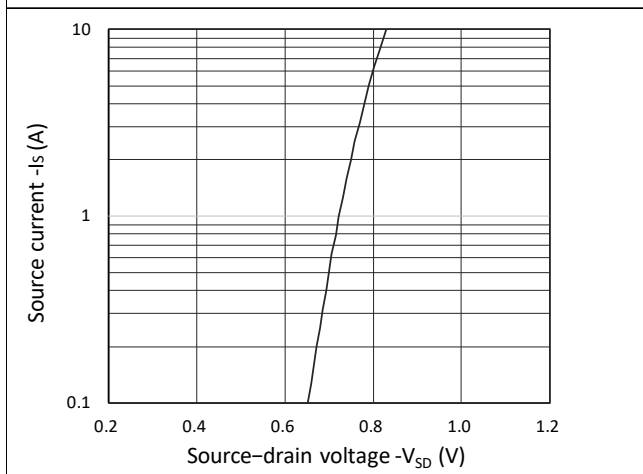


Figure 3. Forward Characteristics of Reverse

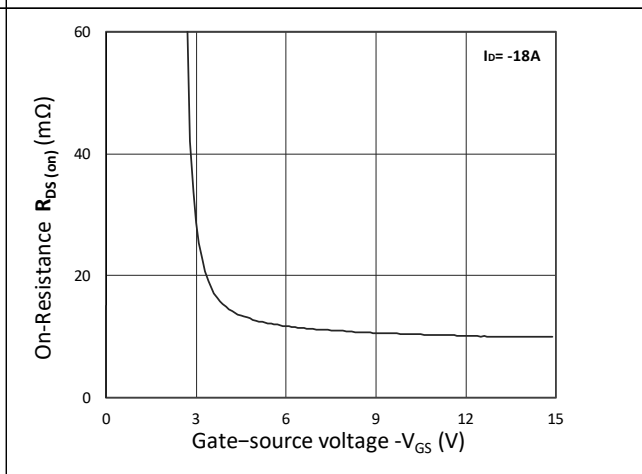


Figure 4. $R_{DS(on)}$ vs. V_{GS}

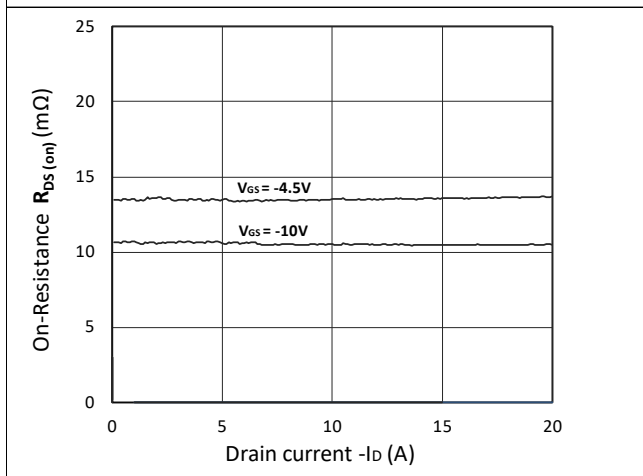


Figure 5. $R_{DS(on)}$ vs. I_D

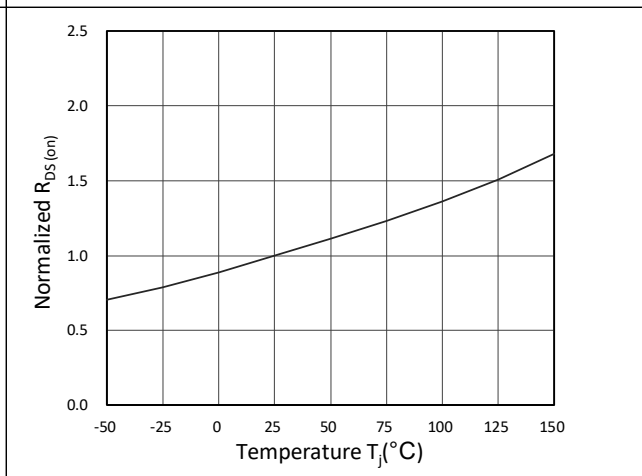


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

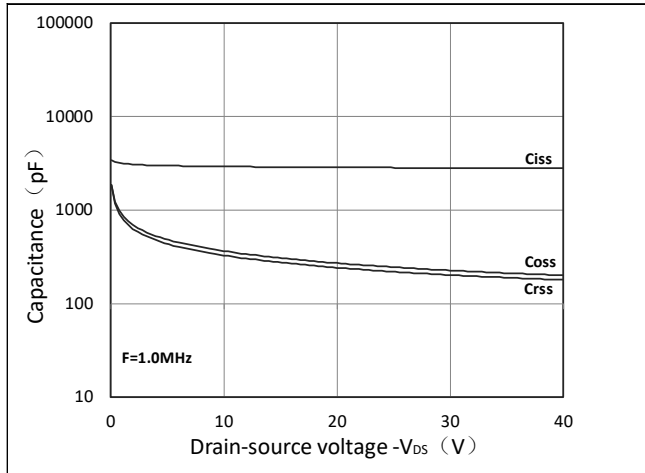


Figure 7. Capacitance Characteristics

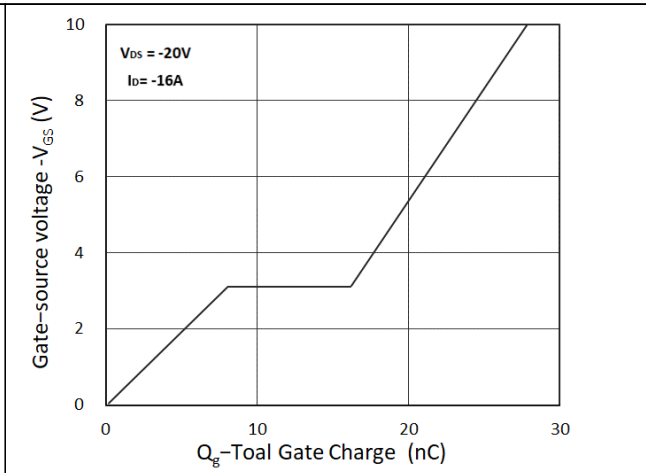


Figure 8. Gate Charge Characteristics

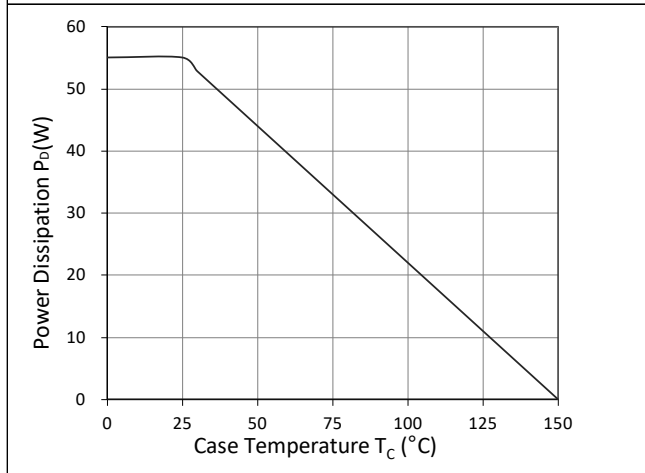


Figure 9. Power Dissipation

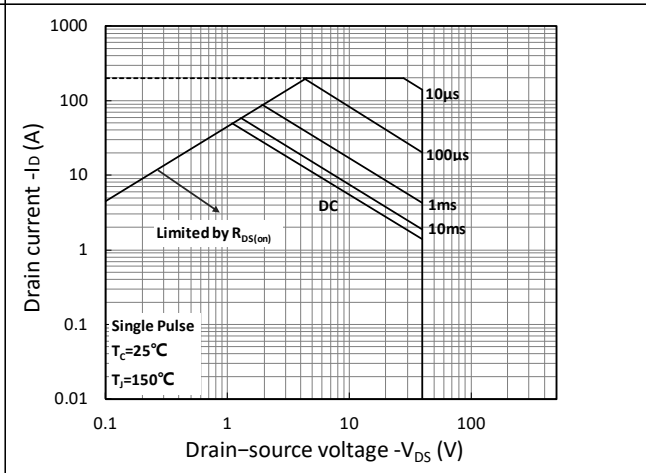


Figure 10. Safe Operating Area

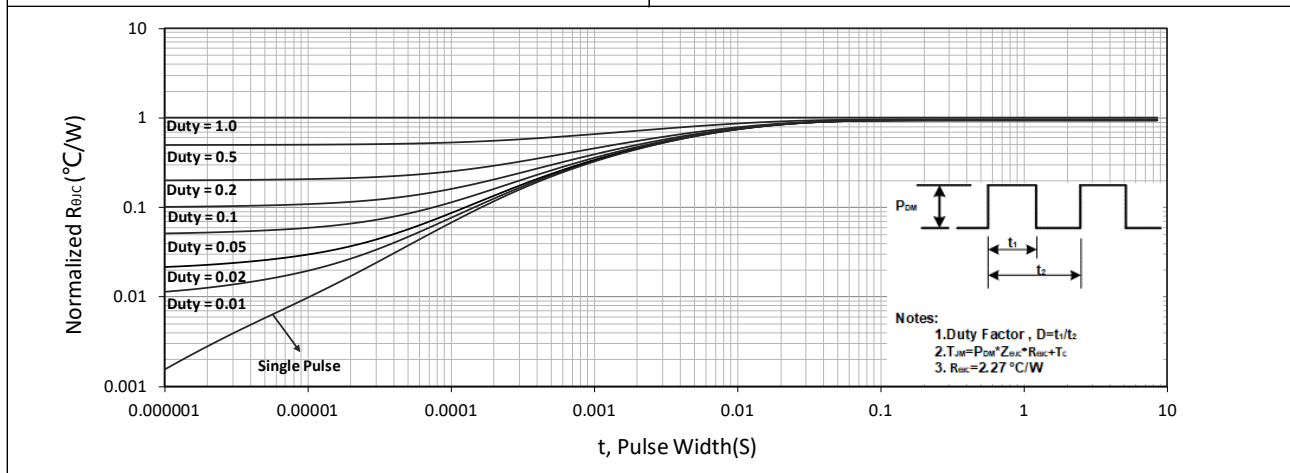


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

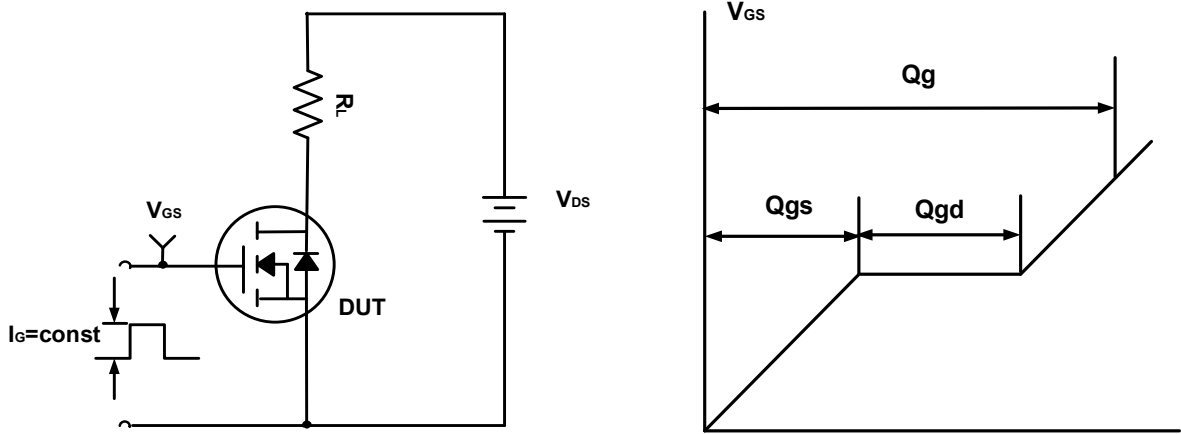


Figure A. Gate Charge Test Circuit & Waveforms

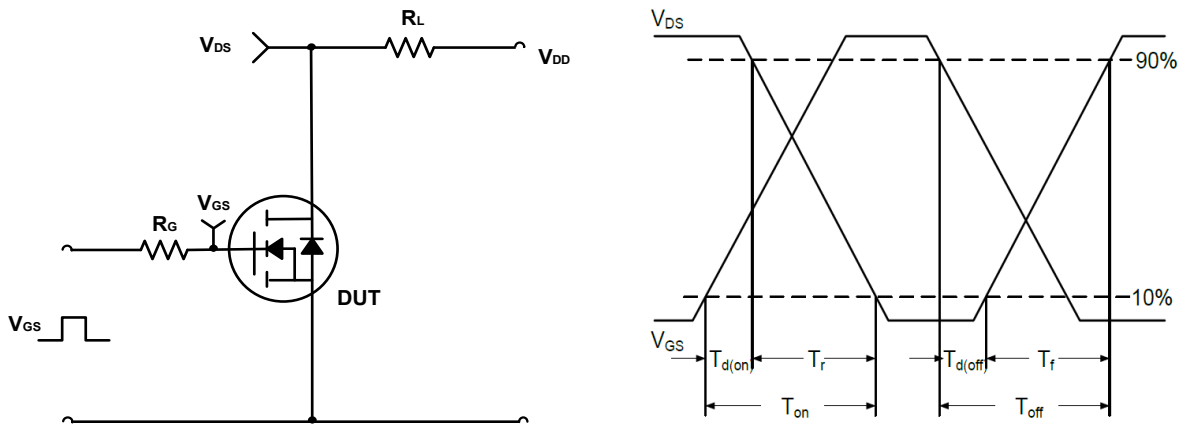


Figure B. Switching Test Circuit & Waveforms

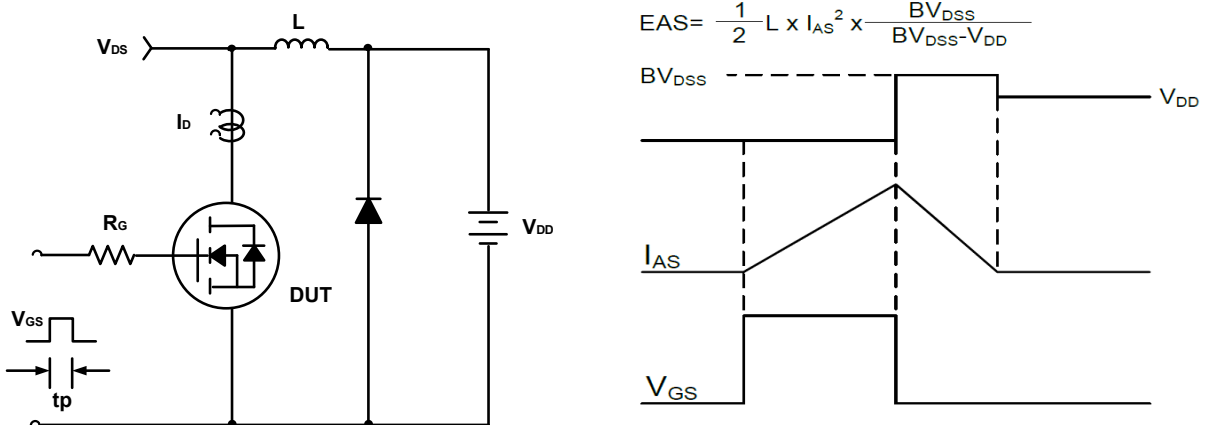


Figure C. Unclamped Inductive Switching Circuit & Waveforms

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